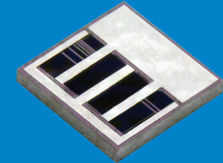




THE VISHAY ADVANTAGE AND WHY IT MATTERS... IN IGBR APPLICATIONS

High Power Back-Contact Thin Film Chip Resistors



Advantage	Why it Matters (Benefit to the Engineer)	Where Should it Be Considered	Best Parameter / Example
Low Inductance	Too much inductance in an IGBT, MOSFET, or power module can cause oscillation, which leads to converter efficiency loss	When designing an IGBT, MOSFET, or power module	One wire bond shortens the wirebond length, which lowers inductance and can handle 6 mil maximum Al wire
High Power	Handles up to 5 W of power in a small case size. Handles the power of MOSFETs and IGBT modules while controlling the current	When designing an IGBT, MOSFET, or power module that is less than or equal to 5 W of power pulsing through	Available in 0202 to 0808 case sizes with 1.8 Ω to 25 Ω resistance values
Reduce Board Space	Small footprint combined with only one wire bond reduces the space it takes on the board	Wherever it is needed to keep inductance low, save time during production, use heavy gage wirebonding, or save space on a circuit board	Available in 0202 to 0808 case sizes with 1.8 Ω to 25 Ω resistance values